

ABSTRACT OF THE DISCLOSURE

The present invention provides a semiconductor device in which occurrence of disclination caused by steps in a contact portion and steps between pixel electrodes is prevented. A 5 method of fabricating a semiconductor device according to the invention includes forming an insulating film 2 on an electrode 1a so as to cover the electrode; forming contact holes 2a and 2b located on the electrode and concave portions 2c and 2d connected to the contact hole; embedding a conductive film 8 in 10 the contact hole and the concave portion and forming a conductive film 8 on the insulating film; and applying the CMP polishing or the etching-back to the conductive film, and thereby forming a pixel electrode made of the conductive films 8a and 8b embedded in the contact hole and the concave portion.